

÷2, ÷4, ÷8 1.1 GHz Low Power Prescaler with Stand-By Mode

MC12093

Description

The MC12093 is a single modulus prescaler for low power frequency division of a 1.1 GHz high frequency input signal. MOSAIC V™ technology is utilized to achieve low power dissipation of 6.75 mW at a minimum supply voltage of 2.7 V.

On-chip output termination provides output current to drive a 2.0 pF (typical) high impedance load. If additional drive is required for the prescaler output, an external resistor can be added parallel from the OUT pin to GND to increase the output power. Care must be taken not to exceed the maximum allowable current through the output.

Divide ratio control inputs SW1 and SW2 select the required divide ratio of ÷2, ÷4, or ÷8.

Stand-By mode is featured to reduce current drain to 50 µA typical when the standby pin SB is switched LOW disabling the prescaler.

Features

- 1.1 GHz Toggle Frequency
- Supply Voltage 2.7 V to 5.5 Vdc
- Low Power 3.0 mA Typical
- Operating Temperature = -40°C to 85°C
- Divide by 2, 4 or 8 Selected by SW1 and SW2 Pins
- On-Chip Termination
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

Table 1. FUNCTIONAL TABLE

SW	SW2	Divide Ratio
L	L	8
H	L	4
L	H	4
H	H	2

1. SW1 & SW2: H = (V_{CC} - 0.5 V) to V_{CC}; L = Open.
2. SB: H = 2.0 V to V_{CC}; L = GND to 0.8 V.

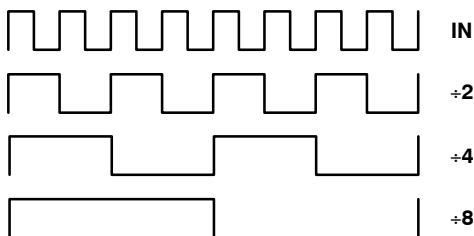
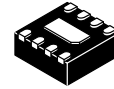


Figure 1. Function Chart

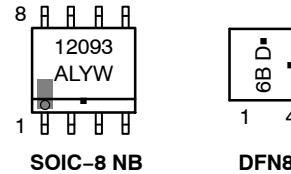


SOIC-8 NB
D SUFFIX
CASE 751-07



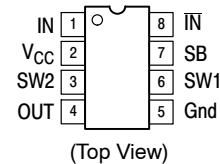
DFN8
MN SUFFIX
CASE 506AA

MARKING DIAGRAM



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

PIN CONNECTIONS



A LOW on the Stand-By Pin 7 disables the device.

ORDERING INFORMATION

Device	Package	Shipping
MC12093DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC12093DR2G	SOIC-8 NB (Pb-Free)	2500 Tape & Reel
MC12093MNR4G	DFN8 (Pb-Free)	1000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MC12093

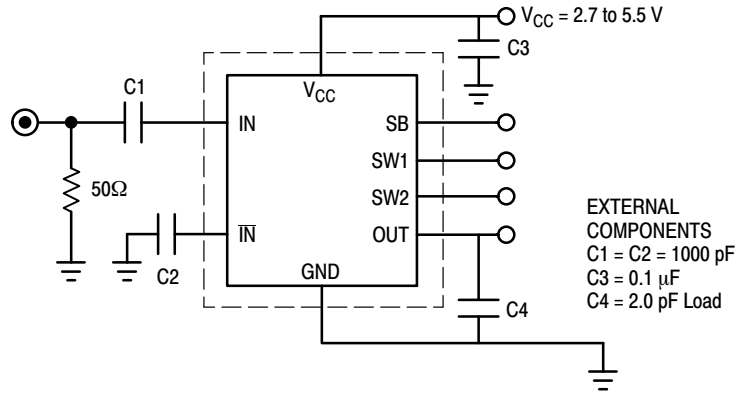


Figure 2. AC Test Circuit

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB DFN8	Level 1 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	125 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

Table 3. MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _{CC}	Power Supply Voltage, Pin 2	-0.5 to 6.0	Vdc
T _A	Operating Temperature Range	-40 to 85	°C
T _{stg}	Storage Temperature Range	-65 to 150	°C
I _O	Maximum Output Current, Pin 4	4.0	mA
θ _{JC}	Thermal Resistance (Junction-to-Case) (Note 1) DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: ESD data available upon request.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power). For DFN8 only, thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

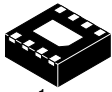
MC12093

Table 4. ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.7$ to 5.5 V; $T_A = -40$ to 85°C)

Symbol	Characteristic	Min	Typ	Max	Unit
ft	Toggle Frequency (Sine Wave)	0.1	1.4	1.1	GHz
I _{CC}	Supply Current	–	3.0	4.5	mA
ISB	Stand-By Current	–	120	200	μA
V _{IH1}	Stand-By Input HIGH (SB)	2.0	–	V _{CC}	V
V _{IL1}	Stand-By Input LOW (SB)	Gnd	–	0.8	V
V _{IH2}	Divide Ratio Control Input HIGH (SW1 & SW2)	V _{CC} – 0.5	V _{CC}	V _{CC} + 0.5	V
V _{IL2}	Divide Ratio Control Input LOW (SW1 & SW2)	OPEN	OPEN	OPEN	
V _{OUT}	Output Voltage Swing (2.0 pF Load)				V _{pp}
	Output Frequency 12.5–350 MHz (Note 1)	0.6	0.80	–	
	Output Frequency 350–400 MHz (Note 2)	0.5	0.70	–	
	Output Frequency 400–450 MHz (Note 3)	0.4	0.55	–	
	Output Frequency 450–550 MHz (Note 4)	0.3	0.45	–	
V _{IN}	Input Voltage Sensitivity				mVpp
	250–1100 MHz	100	–	1000	
	100–250 MHz	400	–	1000	

1. Input frequency 1.1 GHz, +8, minimum output frequency of 12.5 MHz.
2. Input frequency 700–800 MHz, +2.
3. Input frequency 800–900 MHz, +2.
4. Input frequency 900–1100 MHz, +2.

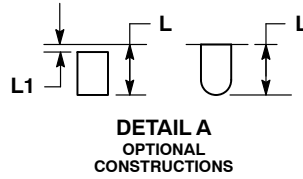
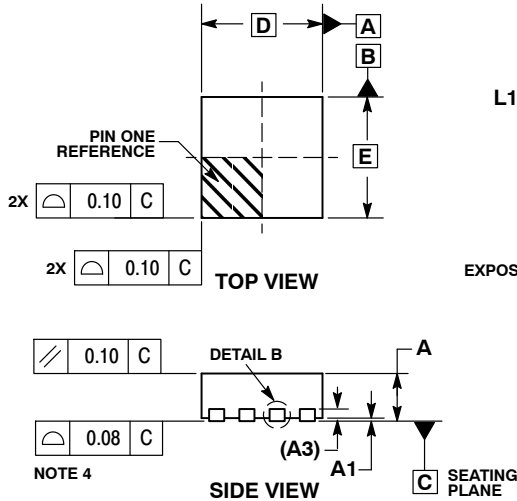
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DFN8 2x2, 0.5P
CASE 506AA
ISSUE F

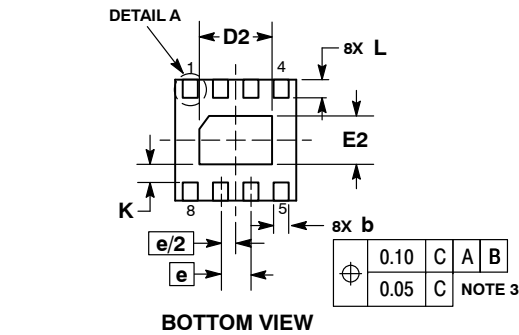
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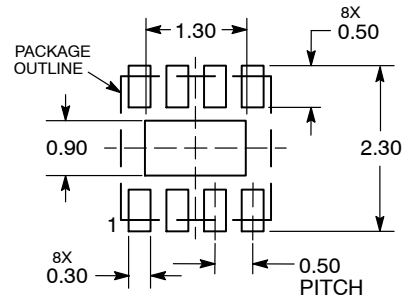
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.00 BSC	
D2	1.10	1.30
E	2.00 BSC	
E2	0.70	0.90
e	0.50 BSC	
K	0.30 REF	
L	0.25	0.35
L1	---	0.10

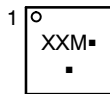


RECOMMENDED
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC
MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SCALE 1:1

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|---|--|--|--|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

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